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10-81-01

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of)
In re PATENT application of:)
Hongyong ZHANG et al.) Art Unit: 2154
Serial No. 09/726,337) Examiner: Unassigned
Filed: 12/01/2000)
For: METHOD FOR PRODUCING A)
SEMICONDUCTOR DEVICE INCLUDING)
DOPING WITH A CATALYST THAT IS A)
GROUP IV ELEMENT)

RECEIVED
OCT 18 2001
Technology Center 2100

PRELIMINARY AMENDMENT

Honorable Commissioner for Patents

Washington, D.C. 20231

Sir:

Please preliminary amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel claim 1 and add new claims 2-23 as follows:

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TC 2800 MAIL ROOM

--2. A semiconductor device comprising:
a source region and a drain region;
a channel formation region provided between said source region and said drain
region and provided in a crystalline semiconductor comprising silicon;
wherein said channel formation region contains an element selected from group
IV elements other than silicon, and
wherein said channel formation region comprises a plurality of crystals provided
in said crystalline semiconductor and extending in a same direction.

3. A semiconductor device comprising:
a source region and a drain region;
a channel formation region provided between said source region and said drain
region and provided in a crystalline semiconductor comprising silicon;

10/17/2001 MWOLDER1 00000068 09726337

01 FC:102
02 FC:103

252.00 OP
36.00 OP